

TABLE OF CONTENTS

PREFACE	iii
TABLE OF CONTENTS	v
SECTION 1: FUNDAMENTALS AND MECHANISMS OF ELECTRODEPOSITION	1
Some Considerations Concerning the Mechanism of Charge-Transfer in Metal Deposition and Dissolution	3
<i>E. Gileadi</i>	
Superconformal Electrochemical Deposition of Gold for Interconnects in Integrated Circuits	13
<i>Z. Hu and T. Ritzdorf</i>	
Quantifying Competitive Adsorption Dynamics in Superfilling Electrolytes	23
<i>T. P. Moffat, D. Wheeler, and D. Josell</i>	
A Comparison Study of MPSA-CI-PEG and SPS-CI-PEG Additive Systems for Copper Electrodeposition	34
<i>M. Tan and J. N. Harb</i>	
Quantitative Monitoring of Copper Electroplating Additives and Their Breakdown Products	41
<i>M.J. West, M.R. Anderson, Q. Wang, T.H. Bailey, A. Rosenfeld, Z.-W. Sun, and K.P. Ta</i>	
Influence of Leveling Agents on Surface Roughness of Electrodeposited Copper Films	57
<i>C. Witt, J. Srinivasan, and R. Carpio</i>	
An In Situ Spectroelectrochemical Investigation into the Electrodeposition of Cu from Acidic Sulfate Solutions in the Presence of Poly(ethylene glycol)	67
<i>B. Bozzini, C. Mele, L. D'Urzo, G. Giovannelli, and S. Natali</i>	
Surface Roughness Evolution during the Initial Stages of Electroplating for Copper Interconnect Metallization	82
<i>E. Webb, C. Gack, and J. Reid</i>	
Impact of Bath Composition on the Purity and Room Temperature Anneal Characteristics of Thin Copper Films	96
<i>J. H. Sukanto and J. D. Reid</i>	
Cross-Sectional Crystallographic Analysis of Copper Electrodeposits for ULSI Metallization by EBSD	108
<i>H.-J. Lee, K.H. Oh, and D.N. Lee</i>	
Analysis of the Bottom-up Fill during Copper Metallization of Semiconductor Interconnects	117
<i>R. Akolkar and U. Landau</i>	

A Case Study in Predictive Three-Dimensional Topography Simulation Based on a Level-Set Algorithm	132
<i>C. Heitzinger, A. Sheikholeslami, J. Fugger, O. Häberlen, M. Leicht, and S. Selberherr</i>	
SECTION 2: ELECTROPLATING TOOLS AND PATTERN EFFECTS	143
Advances in Multilevel Interconnect Technology	145
<i>C. E. Uzoh, T. Wang, H. Talieh, and B. M. Basol</i>	
Study on the Mechanism of Electrochemical Mechanical Deposition of Copper Layers	155
<i>B. M. Basol, C. E. Uzoh, and T. Wang</i>	
Field Effect in “Overplating” Above Damascene Trench Clusters	165
<i>J. O. Dukovic and C. Yu</i>	
Leveling of Electroplated Cu in Damascene Applications	184
<i>J. Reid, E. Webb, J. Sukamto, Y. Takada, and T. Archer</i>	
Uniform Copper Electroplating on Resistive Substrates	193
<i>R. Fang, K. Namiki, P.M. Vereecken, K.T.Kwietniak, B.C. Baker, K. Ide, H. Suzuki, H. Kanda, K. Mishima, K. Musaka, and H. Deligianni</i>	
Unsteady Numerical Simulation of the Mass Transfer within a Reciprocating Paddle Electroplating Cell	205
<i>G. J. Wilson and P.R.. McHugh</i>	
Diffusion Boundary Layer Studies in an Industrial Wafer Plating Cell	224
<i>B. Wu, Z. Liu, A. Keigler, and J. Harrell</i>	
An Investigation of the Effects of Wafer Curvature Changes During Copper Damascene Processing	235
<i>R.A. Carpio, S.-T.L. Dorris, J. Woodring, D. M.Owen and D. Abisia</i>	
SECTION 3: DEPOSITION OF AND ON BARRIERS	249
Formation of Diffusion Barrier Layer on Low-k Material Using Wet Fabrication Process	251
<i>M. Yoshino, T. Yokoshima, T. Osaka, A. Hashimoto, Y. Hagiwara, and I. Sato</i>	
Copper Electrodeposition onto Titanium and Other Substrates: Effect of Bath Composition	264
<i>M. Zheng, M. Willey, H. Song, and A.C. West</i>	
SECTION 4: CLEANING PROCESSES	273
Fluorocarbon Post-Plasma Etch Residue Cleaning With Naphthalenide Radical Anions	275
<i>C. L.Timmons and D. H. Hess</i>	

Etch Rates and Etch Selectivities of p⁺⁺ Doped Si, Undoped Si and Dielectric Films in KOH-Ethylene Glycol-Water Solutions	283
<i>J.S. Starzynski</i>	
SECTION 5: PLANARIZATION	295
Copper Electropolishing and Its Application to ULSI Copper Planarization	297
<i>B. Du and I. I. Suni</i>	
A Comparative Study of Slurry Flow and Transport in CMP Polishing Pads of Three Groove Arrays	308
<i>G. P. Muldowney and D. P. Tselepidakis</i>	
Slurry Backmixing Effects in CMP Rotary and Belt Polishers	318
<i>G. P. Muldowney</i>	
Selection of an Oxidant for Copper CMP	327
<i>M. Anik</i>	
SECTION 6: MEMS AND MAGNETIC MATERIALS	339
MEMS Fabrication for Wireless Communications Using Copper Interconnect Technology	341
<i>H. Deligianni, J.M. Cotte, C.V. Jahnes, P. Buchwalter, N. Hoivik, M. Krishnan, J. Tornello, J.H. Magerlein, and D.E. Seeger</i>	
Magnetically Bistable Actuators for Micro-RF Switch	353
<i>G.D. Gray, and P.A. Kohl</i>	
Electrochemically Formed Biaxial Stress Gradients for Improved Electrostatic Actuation	376
<i>G.D. Gray, M.J. Morgan, and P.A. Kohl</i>	
PVD Silver as a Material of Choice for Microwave Passives in Silicon Technology	393
<i>V. V. Levenets, R. E. Amaya, N. G. Tarr, and T. J. Smy</i>	
Large Volume, High Performance Electroplated Co-Pt(P) Micromagnets for MEMS Applications	404
<i>I. Zana, D. P. Arnold, and M.O. Allen</i>	
Two-Dimensional Computational Model for Electrochemical Micromachining with Ultrashort Voltages Pulses	412
<i>J. A. Kenney and G. S. Hwang</i>	
Comparison of FECO Films Plated from an Ammonium-Containing Sulfate Bath and from a SBA-Containing Sulfate Bath	420
<i>I. Shao, L.T. Romankiw, E.I. Cooper, C. Bonhote, J. Lam, and H. Xu</i>	
Aging of Ni Sulfamate Electrolytes during the Electrodeposition of MEMS Structures	432
<i>J. J. Kelly, S. H. Goods, and A. A. Talin</i>	
Fabrication of Hard Magnetic Micro-arrays by Electroless Codeposition for MEMS Actuators	448
<i>S. Guan and B. J. Nelson</i>	

CoNi/Cu Multilayers by Electrochemical Deposition	457
<i>J. Zhang, M. Moldovan, D. P. Young, and E. J. Podlaha</i>	
Immersion Plating of Bismuth on Tin-Based Alloys to Stabilize Lead-Free Solders	467
<i>E. I. Cooper, C. C. Goldsmith, C. Mojica, S. J. Kilpatrick, and R. J. Alley</i>	
AUTHOR INDEX	475
SUBJECT INDEX	477